

NTE92 (NPN) & NTE93 (PNP) Silicon Complementary Transistors Hi-Fi Power Amp, Audio Output

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

| | |
|--|----------------|
| Collector-Base Voltage, V_{CBO} | 200V |
| Collector-Emitter Voltage, V_{CEO} | 200V |
| Emitter-Base Voltage, V_{EBO} | 6V |
| Collector Current, I_C | 15A |
| Base Current, I_B | 5A |
| Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C | 150W |
| Junction Temperature, T_J | +150°C |
| Storage Temperature Range, T_{stg} | -55° to +150°C |

Note 1. Matched complementary pairs are available upon request (NTE93MCP). Matched complementary pairs have their gain specification (h_{FE}) matched to within 10% of each other.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|----------------------------|-----|-----|-----|------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 200V$ | - | - | 0.1 | mA |
| Emitter Cutoff Current | I_{EBO} | $V_{BE} = 6V$ | - | - | 0.1 | mA |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | $I_C = 50mA$ | 200 | - | - | V |
| DC Current Gain | h_{FE} | $V_{CE} = 4V, I_C = 5A$ | 30 | 120 | - | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 10A, I_B = 1A$ | - | 3 | - | V |
| Transistion Frequency | f_T | $V_{CE} = 12V, I_E = 0.5A$ | - | 20 | - | MHz |

